



IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re: the Application of: Naoya SASHIDA et al.

Group Art Unit: TBA

Serial No.: 10/695,642

Examiner: Unassigned

Filed: October 29, 2003

Confirmation No.: TBA

For: MANUFACTURING METHOD OF SEMICONDUCTOR DEVICE

Attorney Docket No.: 032061

Customer Number: 38834

INFORMATION DISCLOSURE STATEMENT
PURSUANT TO 37 CFR 1.97(b)

Commissioner for Patents
P.O. Box 1450
Alexandria, Virginia 22313-1450

January 5, 2004

Sir:

Applicants direct the attention of the Patent and Trademark Office to the documents listed on the attached Form PTO-1449. A copy of each listed document is attached.

No fee or certification is required in connection with this Information Disclosure Statement, because it is being submitted prior to the issuance of a first official action on the merits or expiration of the three month period following the filing date or the entry of the national stage of the above-captioned application.

The above information is presented so that the Patent and Trademark Office can, in the first instance, determine any materiality thereof to the claimed invention. Applicants respectfully request that the information be expressly considered during the prosecution of this application and that the documents cited in the attached Form PTO-1449 be made of record therein and appear on the first page of any patent to issue therefrom.

Information Disclosure Statement
Attorney Docket No. 032061
Serial No.10/695,642

The Commissioner is authorized to charge our Deposit Account No. 50-2866 for any fee that is required to effect consideration of this statement.

Respectfully submitted,

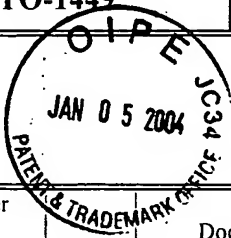
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A handwritten signature in black ink, appearing to read "Stephen G. Adrian", written over the printed name.

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INFORMATION DISCLOSURE CITATION PTO-1449	Atty. Docket No. 032061	Serial No. 10/695,642
	Applicant(s): Naoya SASHIDA et al.	
	Filing Date: October 29, 2003	Group Art Unit: TBD



U.S. PATENT DOCUMENTS

Examiner Initial	Document No.	Name	Date	Class	Subclass	Filing Date (If appropriate)

FOREIGN PATENT DOCUMENTS

Examiner Initial	Document No.	Date	Country	Translation (Yes or No)
	9-053188	2/97	Japan	Abstract

OTHER DOCUMENTS

	<p>Takeshi OHWAKI, Tomoyuki YOSHIDA, Shoji HASHIMOTO, Hideki HOSOKAWA, Yasuichi MITSUSHIMA and Yasunori TAGA; Preferred Orientation in Ti Films Sputter-Deposited on SiO₂ Glass: The Role of Water Chemisorption on the Substrate; Jpn. J. Appl. Phys. Vol. 36 (1997) pp. L154-L157, Part 2, No. 2A, 1 February 1997</p> <p>Makiko KAGEYAMA; Keiichi HASIMOTO and Hiroshi ONODA; Formation of Texture Controlled Aluminum and its Migration Performance in Al-Si/TiN Stacked Structure; IEEE/IRPS; pp 97-101; 1991</p> <p>Tsutomu MITSUZUKA; Highly Preferred [111] Texture of Al Films Deposited on Ultrathin Metal Underlayers; Jpn. J. Appl. Phys. Vol. 31 (1992) pp. L1280 – L1283, Part 2, No. 9A, 1 September 1992</p>
Examiner	Date Considered